



CPH3152

PNP Epitaxial Planar Silicon Transistor

High-Voltage Switching Applications

Applications

- DC / DC converters, relay drivers, lamp drivers, motor drivers.

Features

- Adoption of FBET, MBIT processes.
- Large current capacitance.
- Low collector-to-emitter saturation voltage.
- High-speed switching.
- Ultrasmall package permitting applied sets to be small and slim (mounting height: 0.9mm).
- High allowable power dissipation.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		-150	V
Collector-to-Emitter Voltage	VCE		-150	V
Collector-to-Emitter Voltage	VCEO		-150	V
Emitter-to-Base Voltage	VEBO		-7	V
Collector Current	IC		-1.5	A
Collector Current (Pulse)	ICP		-2.5	A
Base Current	IB		-300	mA
Collector Dissipation	PC	When mounted on ceramic substrate (600mm ² ×0.8mm)	0.9	W
Junction Temperature	TJ		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Marking : BS

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SANYO Semiconductor Co., Ltd.

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN



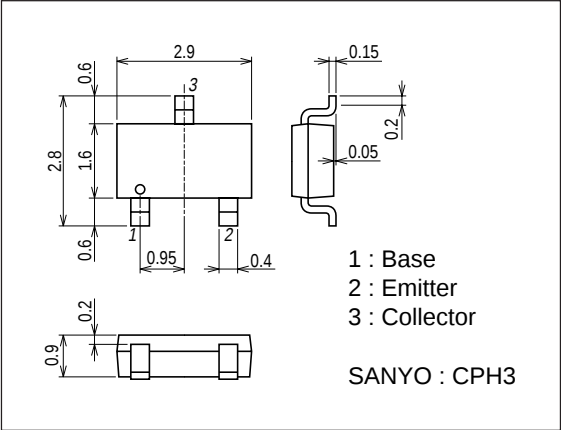
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Electrical Characteristics at Ta=25°C

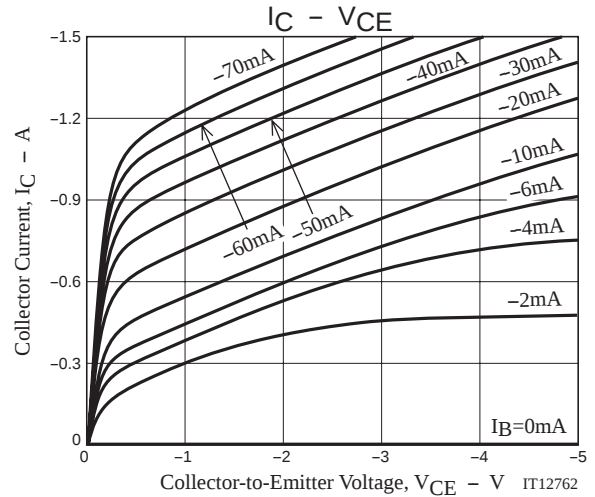
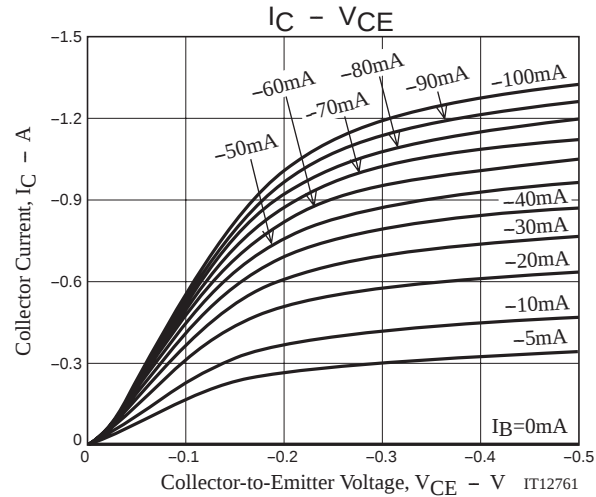
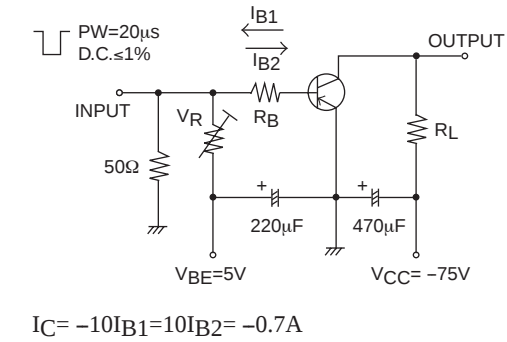
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=-80V, I_E=0A$			-1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-4V, I_C=0A$			-1	μA
DC Current Gain	h_{FE}	$V_{CE}=-5V, I_C=-100mA$	200		560	
Gain-Bandwidth Product	f_T	$V_{CE}=-10V, I_C=-100mA$		70		MHz
Output Capacitance	C_{ob}	$V_{CB}=-10V, f=1MHz$		20		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)1}$	$I_C=-0.75A, I_B=-75mA$		-140	-280	mV
	$V_{CE(sat)2}$	$I_C=-0.5A, I_B=-50mA$		-100	-200	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-0.75A, I_B=-75mA$		-0.85	-1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0A$	-150			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=-100\mu A, R_{BE}=0\Omega$	-150			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1mA, R_{BE}=\infty$	-150			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0A$	-7			V
Turn-ON Time	t_{on}	See specified Test Circuit.		55		ns
Storage Time	t_{stg}	See specified Test Circuit.		840		ns
Fall Time	t_f	See specified Test Circuit.		40		ns

Package Dimensions

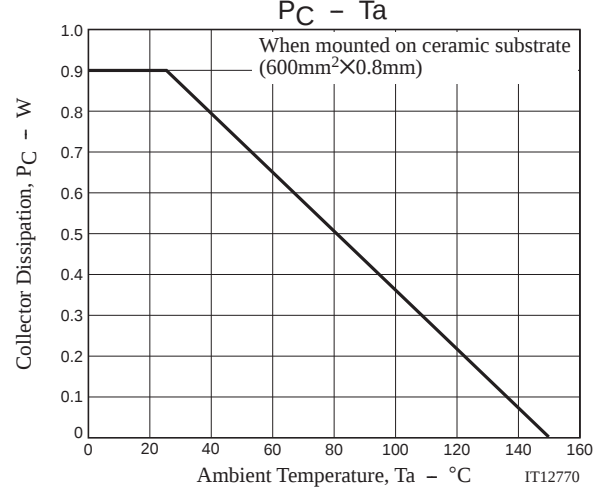
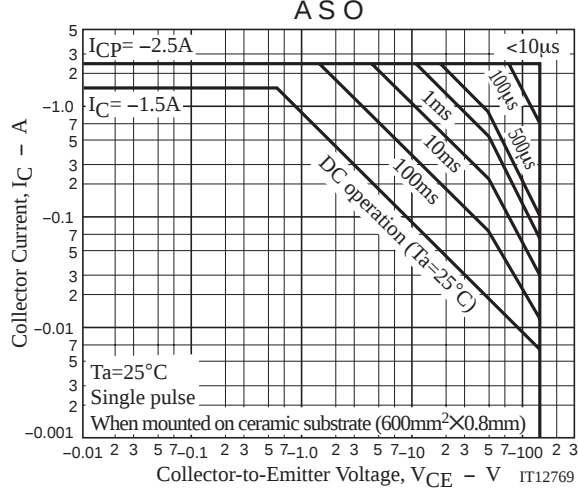
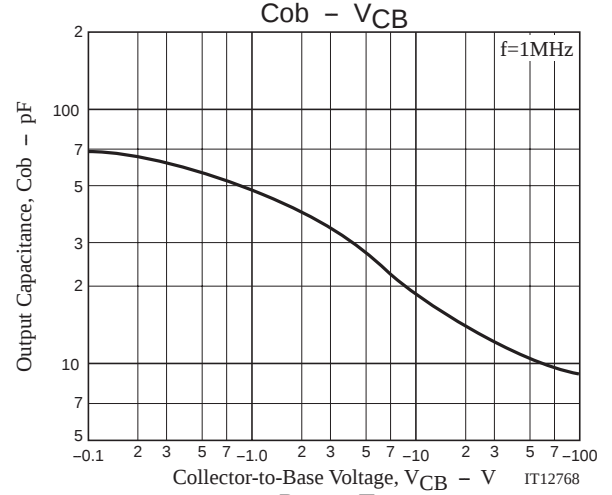
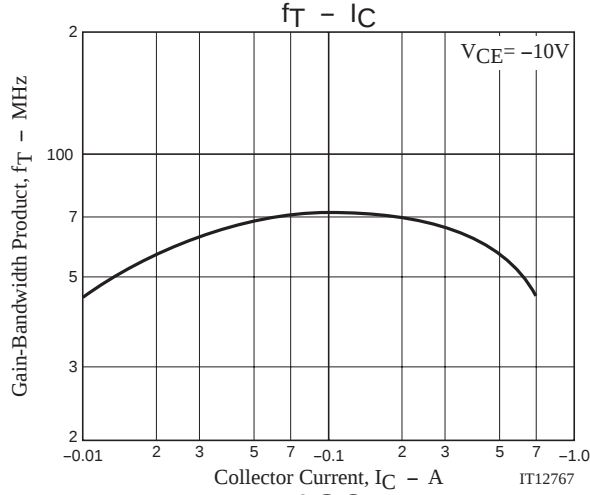
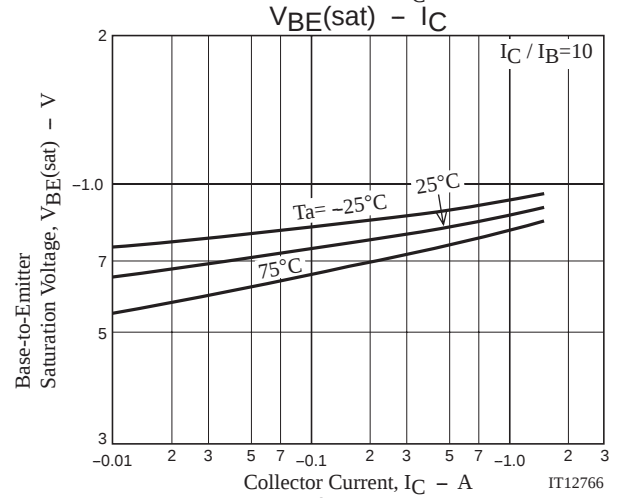
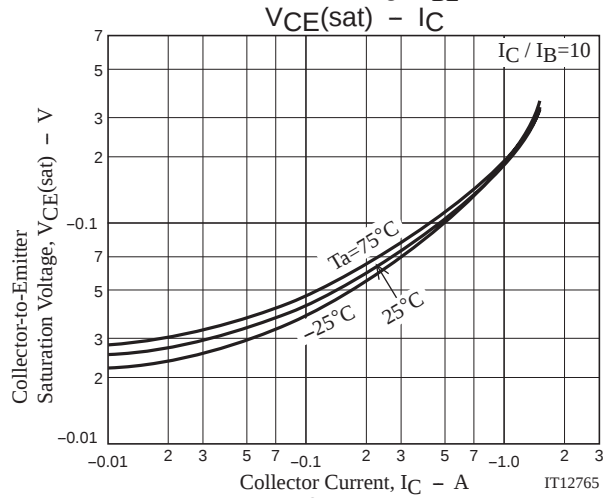
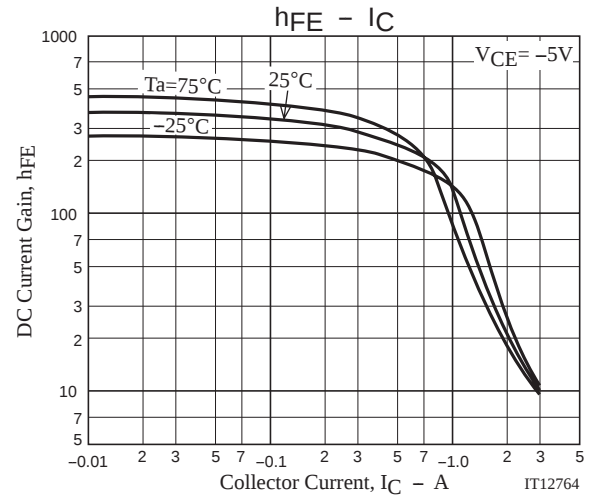
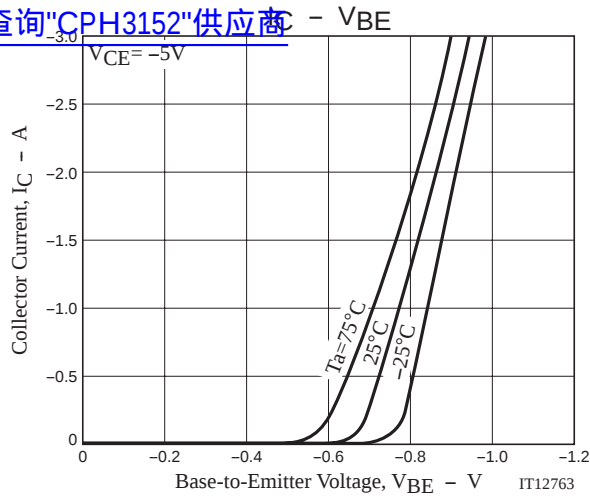
unit : mm (typ)
7015A-003



Switching Time Test Circuit



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